



STH60N10/FI STW60N10

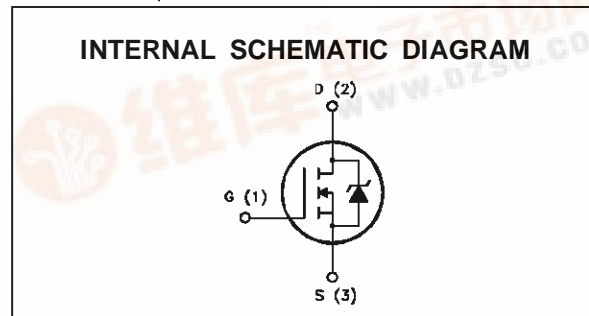
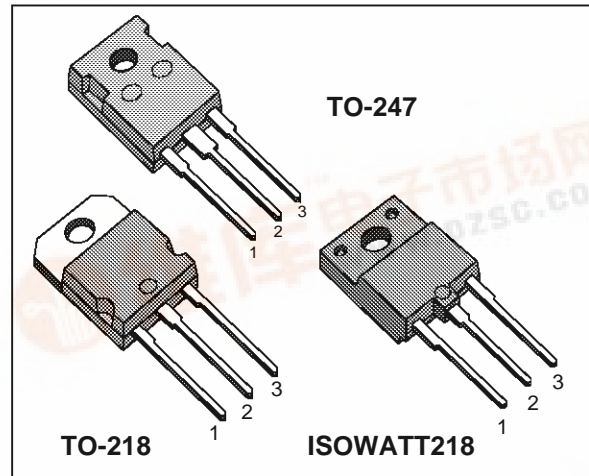
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STH60N10	100 V	< 0.025 Ω	60 A
STH60N10FI	100 V	< 0.025 Ω	36 A
STW60N10	100 V	< 0.025 Ω	60 A

- TYPICAL R_{DS(on)} = 0.02 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- VERY HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STH/STW60N10	STH60N10FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	100		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	60	36	A
I _D	Drain Current (continuous) at T _c = 100 °C	42	22	A
I _{DM} (●)	Drain Current (pulsed)	240	240	A
P _{tot}	Total Dissipation at T _c = 25 °C	200	70	W
	Derating Factor	1.33	0.56	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T _{stg}	Storage Temperature	-65 to 175	-65 to 150	°C
T _j	Max. Operating Junction Temperature	175	150	°C

(●) Pulse width limited by safe operating area

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THERMAL DATA

		TO-218/TO-247	ISOWATT218		
$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.75	1.79	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	30		$^{\circ}\text{C}/\text{W}$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.1		$^{\circ}\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose		300		$^{\circ}\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	60	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 25\text{ V}$)	720	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	180	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100^{\circ}\text{C}$, pulse width limited by T_j max, $\delta < 1\%$)	37	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ $V_{GS} = 0$	100			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}\text{C}$			250 1000	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu\text{A}$	2	2.9	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$ $I_D = 30\text{ A}$ $T_c = 100^{\circ}\text{C}$		0.02	0.025 0.05	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	60			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 30\text{ A}$	25	35		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$		4000	5000	pF
C_{oss}	Output Capacitance			1100	1400	pF
C_{riss}	Reverse Transfer Capacitance			250	350	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 80\text{ V}$ $I_D = 30\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		90 270	130 380	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 80\text{ V}$ $I_D = 60\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		270		A/ μs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		120 16 60	170	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 80\text{ V}$ $I_D = 60\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		200 210 410	280 290 570	ns ns ns

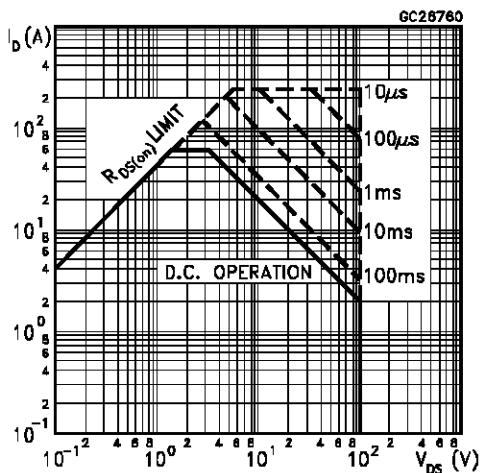
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM(\bullet)}$	Source-drain Current Source-drain Current (pulsed)				60 240	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 60\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 60\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		180 1 11		ns μC A

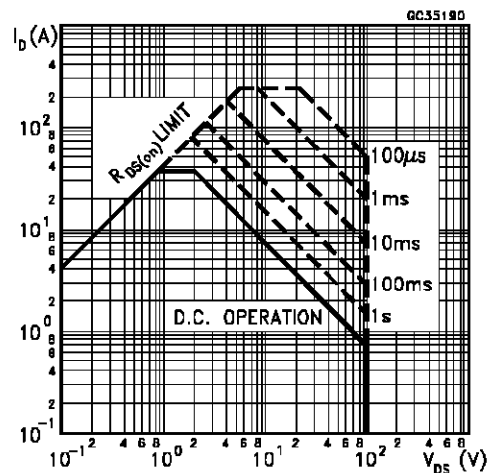
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

Safe Operating Areas For TO-218 and TO-247

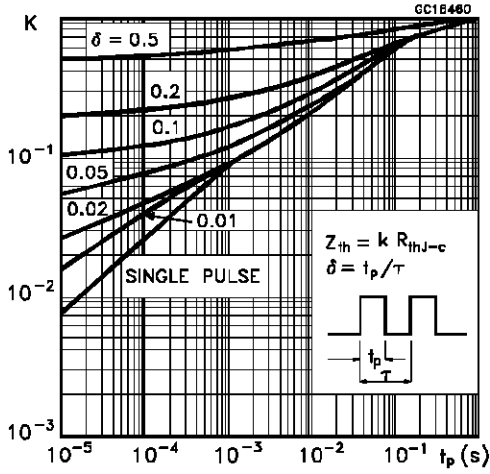


Safe Operating Areas For ISOWATT218

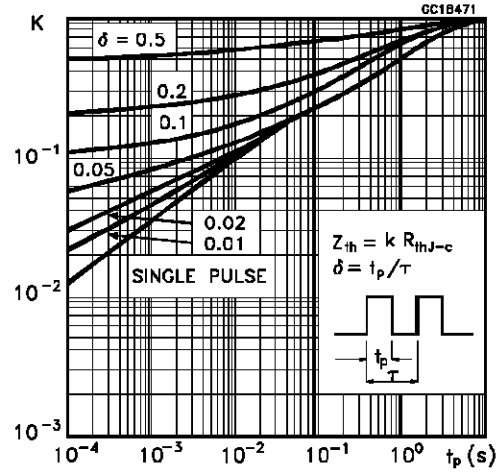


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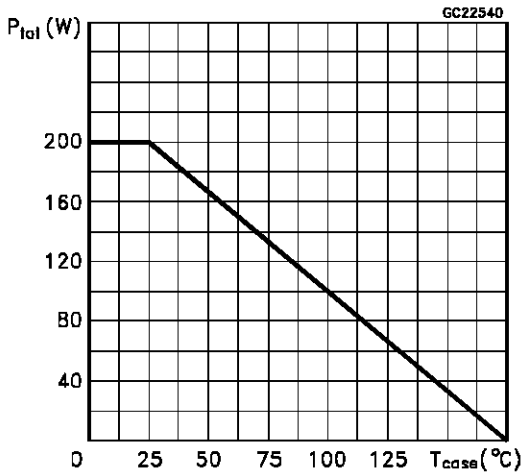
Thermal Impedance For TO-218 and TO-247



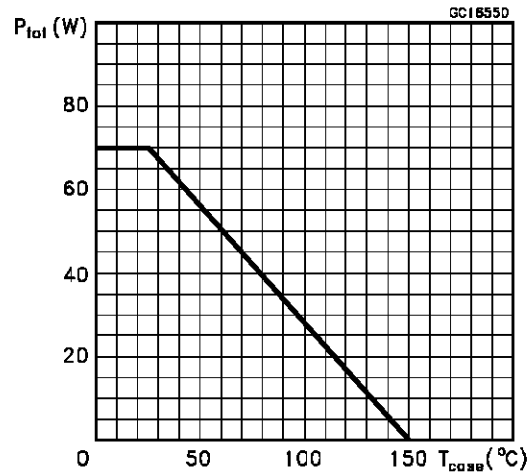
Thermal Impedance For ISOWATT218



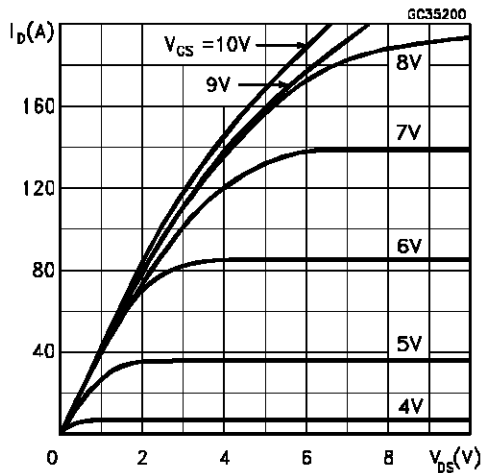
Derating Curve For TO-218 and TO-247



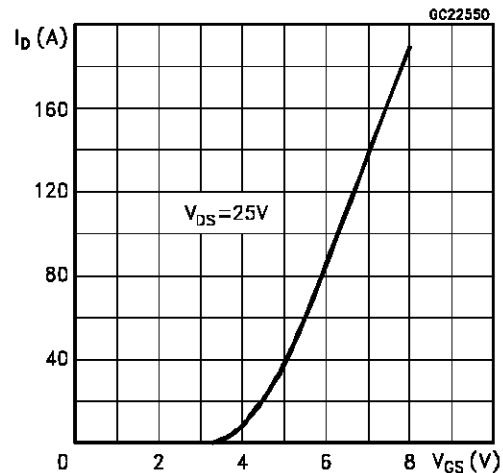
Derating Curve For ISOWATT218



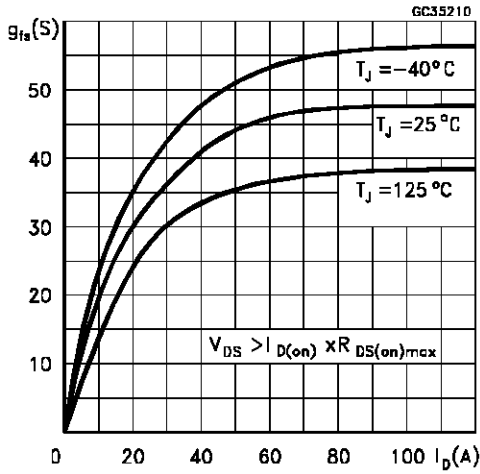
Output Characteristics



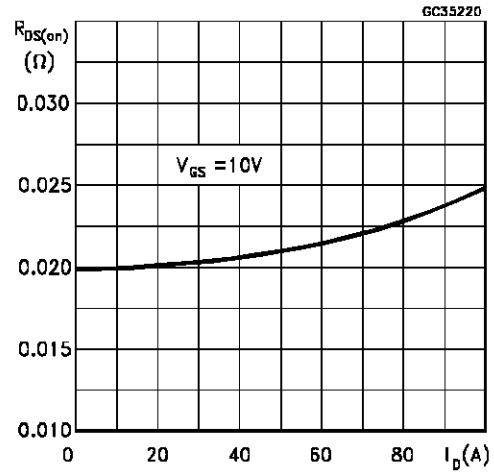
Transfer Characteristics



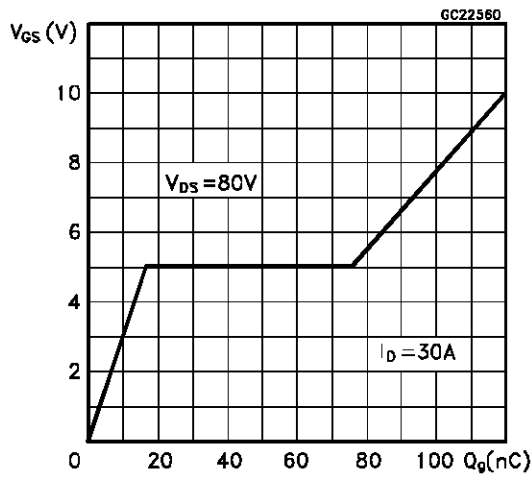
Transconductance



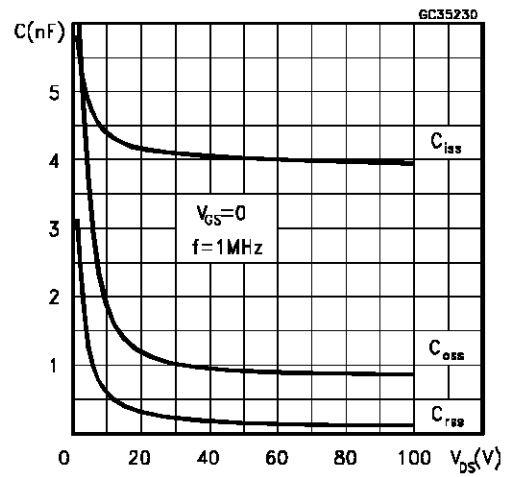
Static Drain-source On Resistance



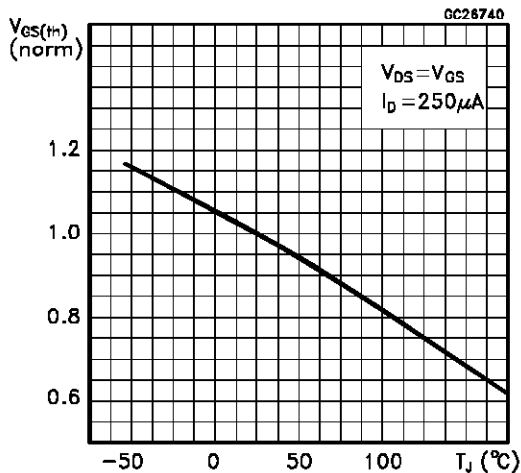
Gate Charge vs Gate-source Voltage



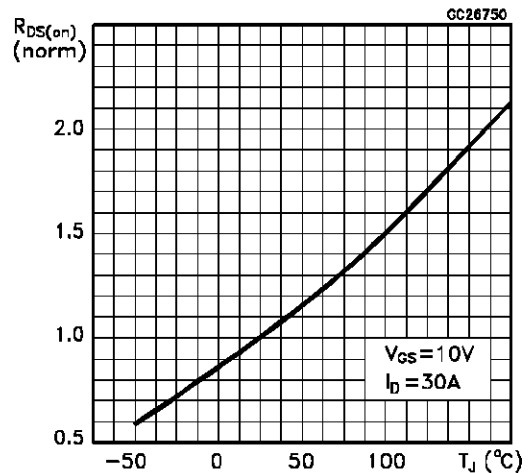
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature

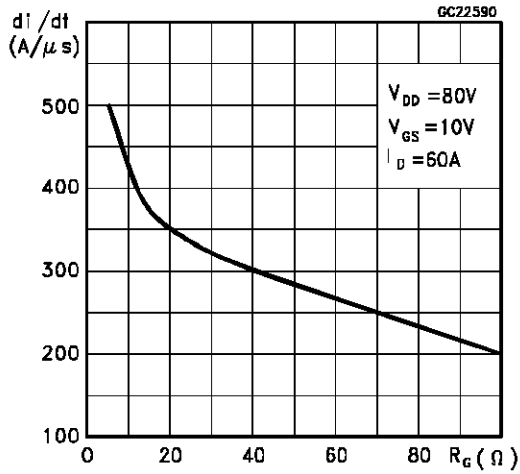


Normalized On Resistance vs Temperature

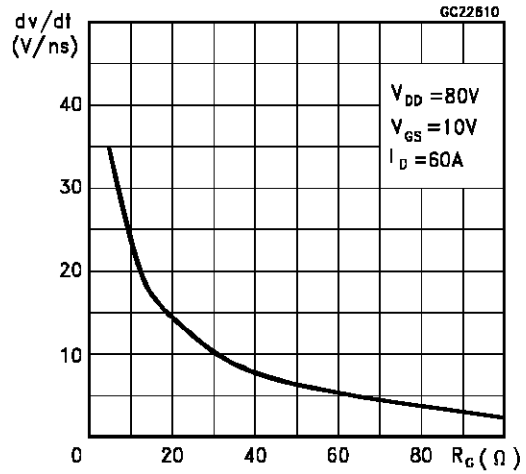


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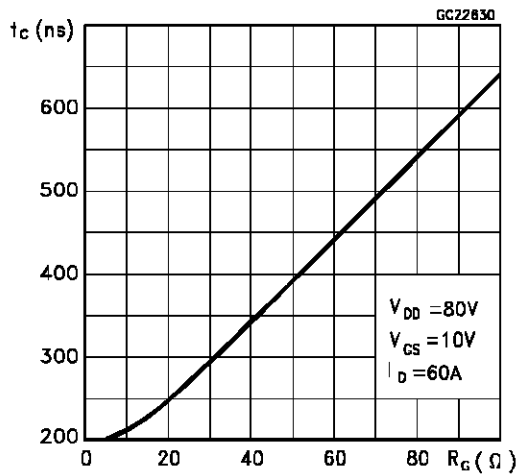
Turn-on Current Slope



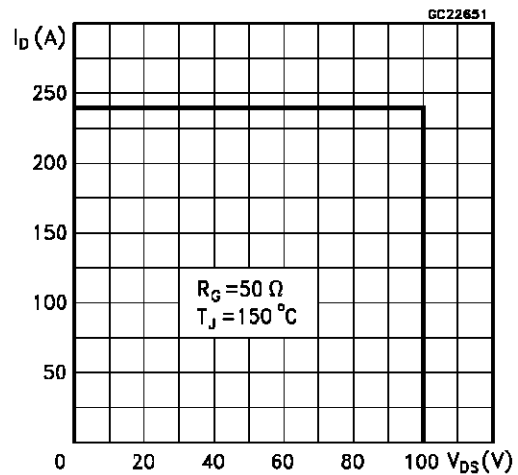
Turn-off Drain-source Voltage Slope



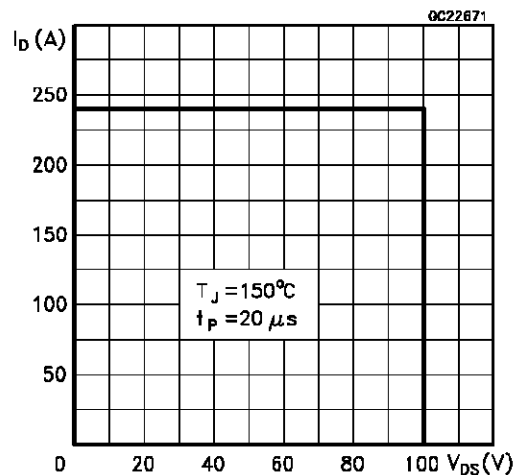
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

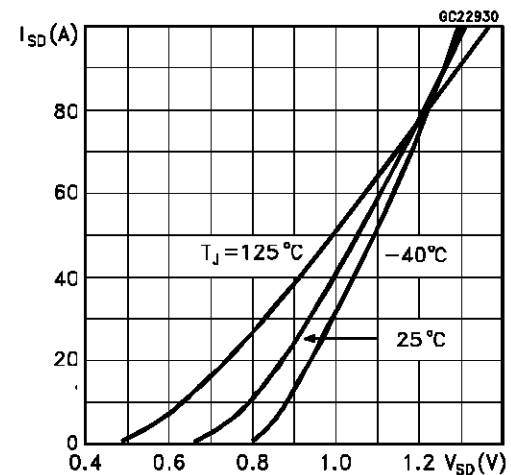


Fig. 1: Unclamped Inductive Load Test Circuits

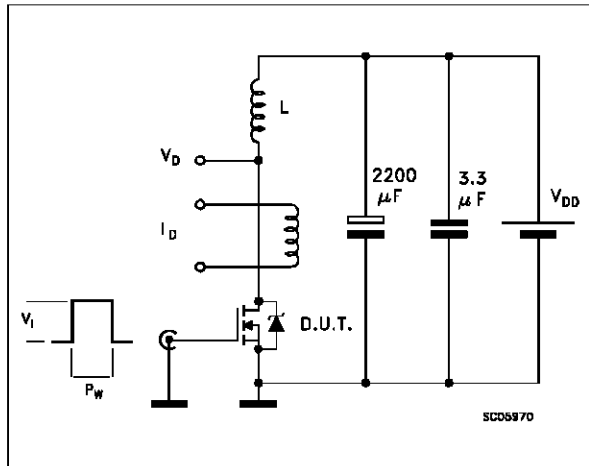


Fig. 2: Unclamped Inductive Waveforms

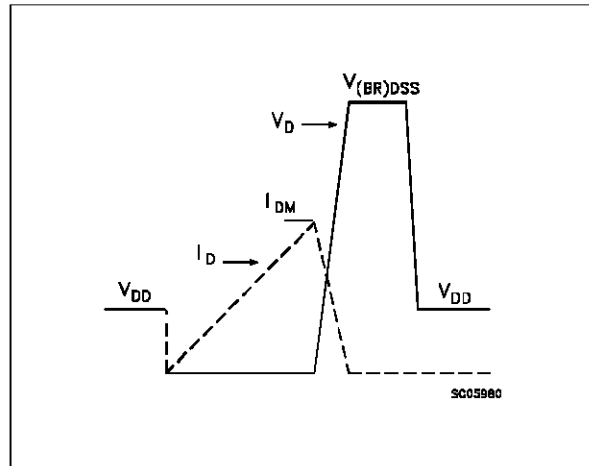


Fig. 3: Switching Times Test Circuits For Resistive Load

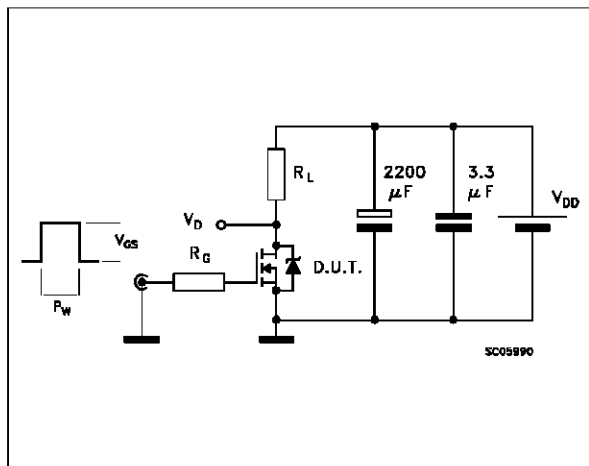


Fig. 4: Gate Charge Test Circuit

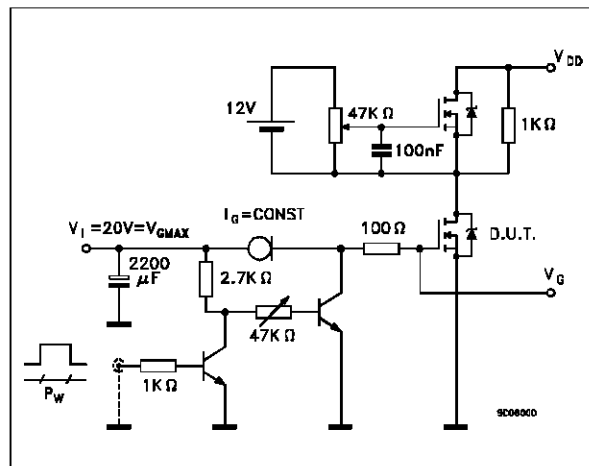
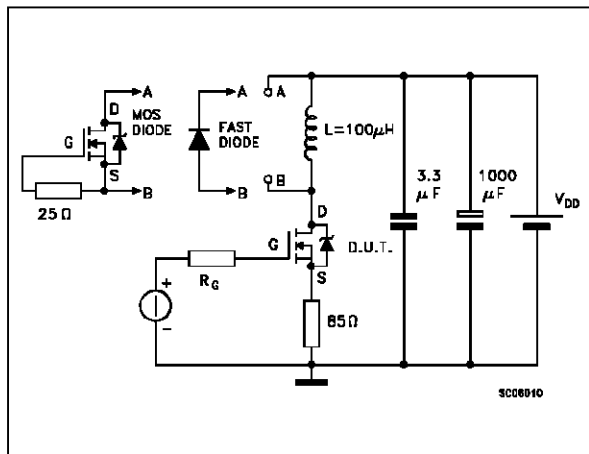
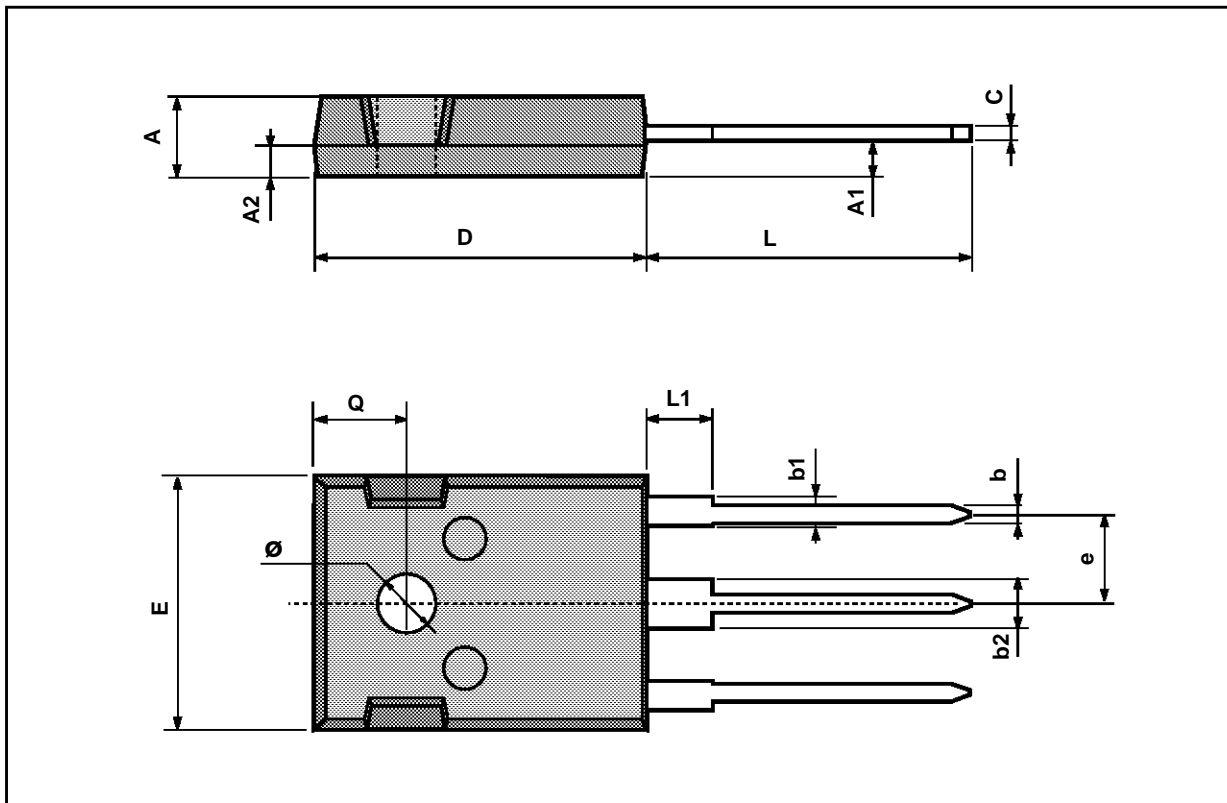


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time



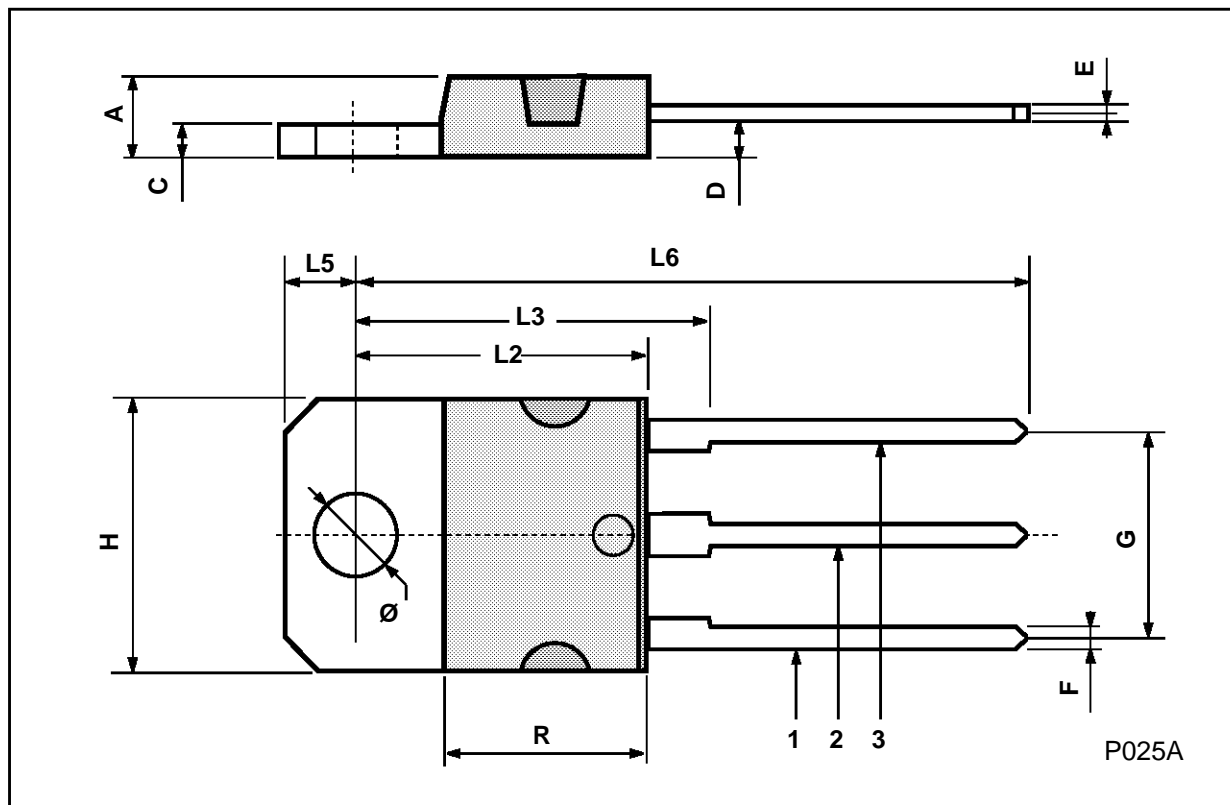
TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.208
A1			2.87			0.113
A2	1.5		2.5	0.059		0.098
b	1		1.4	0.039		0.055
b1			2.25			0.088
b2	3.05		3.43	0.120		0.135
C	0.4		0.8	0.015		0.031
D	20.4		21.18	0.803		0.833
e	5.43		5.47	0.213		0.215
E	15.3		15.95	0.602		0.628
L	15.57			0.613		
L1	3.7		4.3	0.145		0.169
Q	5.3		5.84	0.208		0.230
ØP	3.5		3.71	0.137		0.146



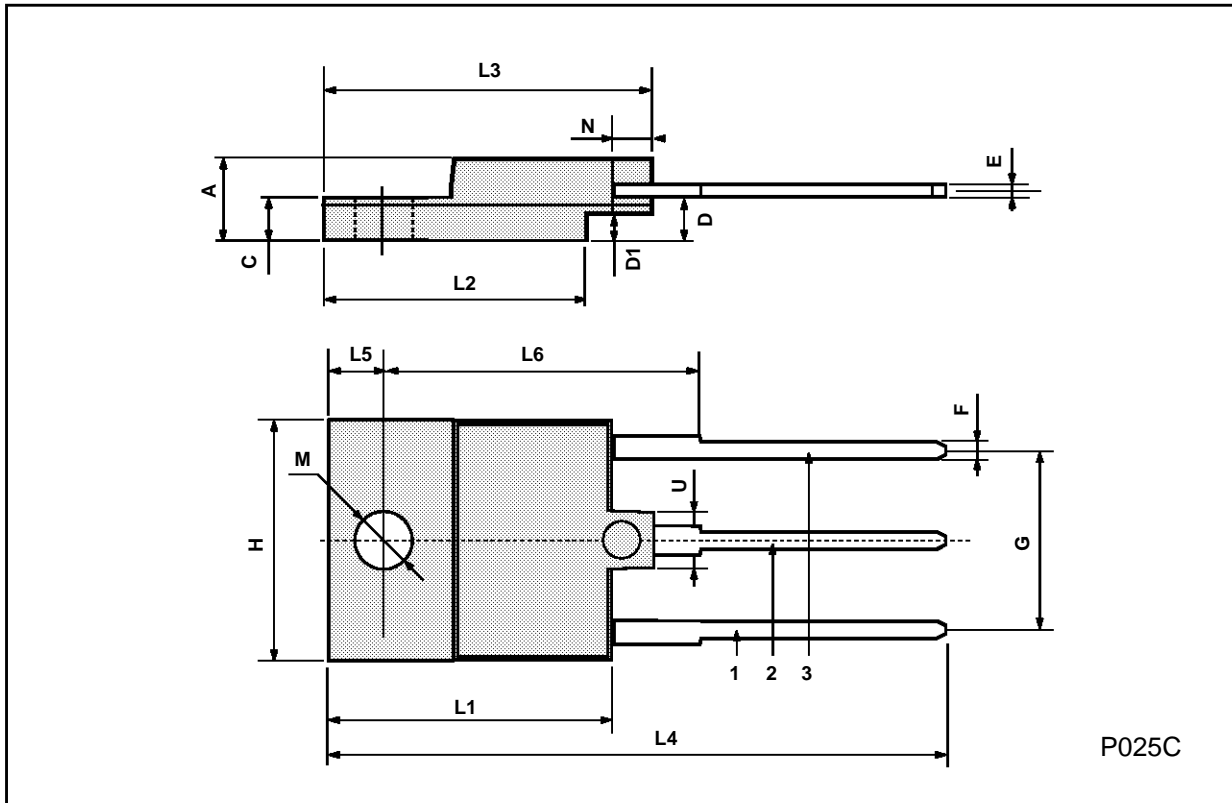
TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	-		16.2	-		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	-		12.2	-		0.480
Ø	4		4.1	0.157		0.161



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.45		1	0.017		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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